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Amphoteric Be in GaN: Experimental Evidence for Switching between Substitutional and Interstitial Lattice Sites

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We show that Be exhibits amphoteric behavior in GaN, involving switching between substitutional and interstitial positions in the lattice. This behavior is observed through the dominance of BeGa in the positron annihilation signals in Be-doped GaN, while the emergence of V\textsubscript{Ga} at high temperatures is a consequence of the Be impurities being driven to interstitial positions. The similarity of this behavior to that found for Na and Li in ZnO suggests that this could be a universal property of light dopants substituting for heavy cations in compound semiconductors.

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The quest for efficient p-type dopants in wide band gap compound semiconductors, such as GaN and ZnO, has been long and largely unsuccessful. Approaches adopted from semiconductor technology based on Si and GaAs, where suitable donors and acceptors with low activation energies are found in the periodic table right next to the atoms constituting the host lattice, have essentially failed. For example, the state-of-the-art choice for p-type doping of GaN is Mg, a light alkaline earth metal, whose activation efficiency is only about 1%. Remarkably, even though Mg has already been utilized as the p-type dopant in GaN devices for decades, both the exact lattice location and electronic activity of this impurity are still debated [1–4]. The relatively high activation energy and passivation–compensation issues result in poor activation of Mg—better p-type dopants would clearly be welcome.

Interest in Be as a dopant in GaN has recently reemerged thanks to the appearance of encouraging reports from experimental activities [5–9] and novel predictions with improved theoretical methods [10]. While p-type GaN may not be achieved with Be doping, semi-insulating material is highly desirable for manufacturing high-electron-mobility transistors, for example. The dominant lattice locations and related optical signatures [7,9], particularly self-compensation through the balance between substitutional and interstitial positions [10], need to be understood in detail for efficient use of Be in GaN-based devices.

In this Letter, we show that Be impurities exhibit amphoteric behavior in GaN, similar to what has been found for Li impurities in ZnO [11,12] and for certain vacancy-type defects in III-V semiconductors [13,14]. This finding suggests a universal property of small elements substituting for large cation atoms in these compounds, that is, the rise of a competition between substitutional and interstitial lattice sites. We arrived at these conclusions by performing positron annihilation spectroscopy [15] on Be-doped GaN thin films grown by molecular beam epitaxy (MBE) and bulk crystals grown by the high nitrogen pressure solution (HNPS) method. Our experimental approach is augmented by state-of-the-art modeling of positron states and annihilation signals. In addition, positrons can provide detailed information on small substitutional elements [12].

The Be-doped GaN MBE thin films were grown at 675–770°C on GaN templates (Ga-polar samples) or directly on sapphire substrates (N-polar samples) [16]. Postgrowth heat treatments were performed on the Ga-polar samples in N\textsubscript{2} ambient at a temperature of 900°C for 2 h. The growth conditions were similar for all the thin films, except for the sample N2 where the Ga flux was significantly lower (9 vs \(16 \times 10^{-7}\) Torr). The Ga-polar samples were found to be semi-insulating before and after postgrowth heat treatment, except for Ga5 (as-grown) exhibiting n-type behavior. The crystallization processes of the HNPS bulk crystals are described in Refs. [7,17]. Be concentrations were determined by secondary ion mass spectrometry. Table I summarizes the impurity concentrations and the relative S and W Doppler broadening parameters (reference: p-type GaN) in the samples.

We performed both conventional and coincidence Doppler broadening measurements of positron annihilation radiation with a variable-energy positron beam. We used high purity germanium (HPGe) detectors with an energy resolution of 1.2 keV at 511 keV. The integration windows for the S and W parameters were set to \([p_L] \leq 0.4\) a.u. and 1.6 a.u. < \([p_L] < 4.0\) a.u., respectively. We performed positron lifetime experiments on the HNPS GaN samples with a standard temperature-controlled digital spectrometer in collinear geometry and time resolution of 250 ps.
TABLE I. Be content and relative $(S, W)$ parameters for the Be-doped GaN samples. Samples Ga1–Ga5 are Ga-polar and N1–N3 are N-polar thin films. “A” stands for annealed. HNPS low-O is a low-oxygen bulk crystal with $[O] \sim 10^{19}$ cm$^{-3}$. The samples that do not follow the general trends discussed in the text are marked with $\ast$.

<table>
<thead>
<tr>
<th>Sample</th>
<th>[Be] (cm$^{-3}$)</th>
<th>$S$ relative</th>
<th>$W$ relative</th>
</tr>
</thead>
<tbody>
<tr>
<td>Ga1</td>
<td>$5 \times 10^{17}$</td>
<td>1.000(2)</td>
<td>0.961(7)</td>
</tr>
<tr>
<td>Ga1A*</td>
<td>$5 \times 10^{17}$</td>
<td>1.002(2)</td>
<td>0.950(7)</td>
</tr>
<tr>
<td>Ga2</td>
<td>$1 \times 10^{18}$</td>
<td>0.997(2)</td>
<td>0.963(7)</td>
</tr>
<tr>
<td>Ga2A</td>
<td>$1 \times 10^{18}$</td>
<td>1.008(2)</td>
<td>0.919(7)</td>
</tr>
<tr>
<td>Ga3</td>
<td>$2 \times 10^{18}$</td>
<td>0.996(2)</td>
<td>0.969(7)</td>
</tr>
<tr>
<td>Ga3A</td>
<td>$2 \times 10^{18}$</td>
<td>1.008(2)</td>
<td>0.917(7)</td>
</tr>
<tr>
<td>Ga4</td>
<td>$4 \times 10^{18}$</td>
<td>0.996(2)</td>
<td>0.967(7)</td>
</tr>
<tr>
<td>Ga4A</td>
<td>$4 \times 10^{18}$</td>
<td>1.007(2)</td>
<td>0.904(7)</td>
</tr>
<tr>
<td>Ga5</td>
<td>$1 \times 10^{19}$</td>
<td>1.003(2)</td>
<td>0.942(7)</td>
</tr>
<tr>
<td>Ga5A</td>
<td>$1 \times 10^{19}$</td>
<td>1.006(2)</td>
<td>0.908(7)</td>
</tr>
<tr>
<td>N1</td>
<td>$7 \times 10^{18}$</td>
<td>0.999(2)</td>
<td>0.959(7)</td>
</tr>
<tr>
<td>N2*</td>
<td>$7 \times 10^{18}$</td>
<td>1.013(2)</td>
<td>0.921(7)</td>
</tr>
<tr>
<td>N3</td>
<td>$7 \times 10^{18}$</td>
<td>1.003(2)</td>
<td>0.938(7)</td>
</tr>
<tr>
<td>HNPS low-O</td>
<td>$3 \times 10^{19}$</td>
<td>1.008(3)</td>
<td>0.92(1)</td>
</tr>
</tbody>
</table>

(FWHM). More details on the experimental techniques and data analysis can be found in Ref. [15].

We used *ab initio* electronic structure calculations to model the positron annihilation parameters in the GaN lattice and at different kinds of relaxed defect structures, taking into account the forces exerted on the ions by the localized positron [18]. The valence electron densities were obtained self-consistently via the local-density approximation (LDA), employing the projector augmented-wave (PAW) method [19] and the plane-wave code VASP [20]. The positron states and annihilation characteristics were determined using the LDA [21] and the state-dependent scheme [22] for the momentum densities of annihilating electron-positron pairs. We use a 96-atom GaN wurtzite supercell and check the positron localization to substitutional BeGa with a 768-atom cell. The Doppler spectra were computed using reconstructed PAW orbitals [18] and atomic orbitals for the core electrons, and finally convoluted with the experimental resolution.

Figure 1 presents the $S$ parameter measured as a function of positron implantation energy (implantation depth) in selected MBE-grown Be-doped GaN thin films before and after annealing. The dashed line corresponds to the bulk $S$ parameter value of the $p$-type GaN reference.

FIG. 1. The $S$ parameter measured as a function of positron implantation energy (implantation depth) in selected MBE-grown Be-doped GaN thin films before and after annealing. The dashed line corresponds to the bulk $S$ parameter value of the $p$-type GaN reference.

The data points of the Be-doped GaN samples do not fall on the line connecting the GaN lattice to $V_{Ga}$ nor above it (nor to the right of it), as would be typical of GaN containing...
either in-grown or processing-induced V\textsubscript{Ga}-related defects [28–30]. Instead, all the data points from the Be-doped samples are located in the vicinity of the calculated points for BeGa-related defects. These observations strongly suggest that the defects detected by positrons in Be-doped GaN are of BeGa nature. The data points from the as-grown Be-doped GaN thin films are clustered towards the upper left, while the data points from the annealed samples are clustered towards the lower right with the data point obtained in the Be-doped GaN bulk crystal (low-O). The samples Ga1A and N2 do not follow the general trend. Yet the point for Ga1A is towards the lower right from Ga1, while the growth conditions for N2 were different compared to the rest of the thin films.

Figure 3 displays ratio curves: coincidence Doppler broadening experiments in Ga-polar samples and from theoretical calculations. The comparison of experimental and theoretical data clearly shows that defects related to Be\textsubscript{Ga} are detected in Be-doped GaN.

features in these curves, in order of importance, are the intensity close to 0 a.u. (the \(S\)-parameter region), the intensity above 2 a.u. (the \(W\)-parameter region), the relationship between these two intensities, and the shoulder-like feature in the range of 1–2 a.u. [15]. It is clear that the defects observed in the as-grown sample are related to Be\textsubscript{Ga}, Be\textsubscript{Ga}-\textsubscript{H} or Be\textsubscript{Ga}-\textsubscript{O\textsubscript{N}}, as the ratio curves for all the other defects are notably different. After annealing, the positron data obtained in the Be-doped samples are clearly affected by V\textsubscript{Ga}-related defects, while still resembling the Be\textsubscript{Ga} signals. Importantly, there is no evidence for the presence of Be\textsubscript{Ga} complexed with nitrogen vacancies, as seen also in Fig. 2 where the point characteristic of the Be\textsubscript{Ga}-V\textsubscript{N} complex is far to the right from the experimental data.

Through positron lifetime experiments in HNPS-grown GaN:Be bulk crystals, we have further verified our interpretation of substitutional Be\textsubscript{Ga} acting as an efficient positron trap in GaN. Figure 4 shows the average positron lifetime measured as a function of temperature in two different crystals. One is a high-oxygen (<10\textsuperscript{20} cm\textsuperscript{-3}) crystal already studied earlier [31], and the other is a state-of-the-art low-oxygen (<10\textsuperscript{19} cm\textsuperscript{-3}) crystal [7]. The figure also shows the data from a highly Mg-doped ammonothermally grown GaN crystal that provides the values characterizing the GaN lattice [32]. The Be-doped crystals show a 5–10 ps longer single lifetime than in the GaN lattice at temperatures below 300 K. The high-O HNPS GaN clearly also contains Ga vacancy-related defects that become visible at temperatures above 300 K, as seen through the emergence of the second lifetime component of about 230 ps (Fig. 4 top). The theoretical predictions for
the BeGa-related defects (Fig. 2) match the experimental observation and also rule out the BeGa – V_N complexes.

Our data show that positron annihilation is dominated by BeGa-related defects in all the as-grown Ga-polar Be-doped MBE-grown thin films, in the N-polar samples N1 and N3, and in the Be-doped HNPS GaN low-O bulk crystal. The strength of the signal implies that the concentration of these defects is at least in the 10^{17} \text{cm}^{-3} range, consistent with the lowest Be doping. In addition to the BeGa signal, V_Ga-type defects produce a significant signal in the annealed Ga-polar samples, in the N-polar sample N2, and in the Be-doped HNPS GaN high-O single crystal. Generally, doping with Be makes GaN semi-insulating, as is the case with the present samples as well. The associated relatively low-lying Fermi level makes the thermal formation of acceptorlike V_Ga very unlikely due to their high formation energy\[33,34\]. Hence the nonobservation of V_Ga in most of the as-grown MBE samples comes as little surprise. The sample N2 was grown at a significantly lower Ga flux, explaining the presence of a V_Ga-related signal in this sample. The observation of significant concentrations of V_Ga-related defects in MBE thin films after thermal annealing at 900°C and in the high-O HNPS bulk crystal calls for further consideration.

Efficient generation of acceptor-type V_Ga can proceed either through the direct mechanism of Be_Ga → V_Ga + Be_i or indirectly through thermal vacancy formation if the Fermi level is sufficiently close to the conduction band minimum during the heat treatment. The latter mechanism also requires that Be impurities are efficiently excited from the substitutional to interstitial positions, since Be_Ga are acceptors but Be_i are double donors\[10\]. Hence, the presence of V_Ga after annealing is an indication of Be switching between substitutional and interstitial sites. As the samples are semi-insulating after the heat treatment, most of the Be impurities regain their substitutional position during cooling. It should be noted that with the present Be concentrations, it is sufficient that only a small fraction, of the order of 10%, of Be is not converted back to BeGa during cooling for the V_Ga concentration to have the effect on the positron data observed in Fig. 3. The emergence of the V_Ga-related defects after annealing explains the appearance of additional donor-acceptor pair photoluminescence signatures found in the MBE-grown Be-doped thin films\[16\].

The estimation of V_Ga equilibrium concentration provides further insight into the defect formation mechanism. The formation energy of triple acceptor V_Ga has been determined\[35\] to be E_f = 3.0 ± 0.5 eV at the Fermi level position $E_F = 0.5$ eV, corresponding to $E_f = 1.5 ± 0.5$ eV when the Fermi level $E_F$ coincides with the conduction band minimum $E_C$. Assuming a formation entropy of $S = 5 ... 10 k_B$, the upper limit of the equilibrium concentration of V_Ga at a temperature of 900°C can be estimated as $3 \times 10^{16}$ cm$^{-3}$. For the V_Ga-type signal to be significant after annealing, the concentration of the thermally generated V_Ga must be of the same order of magnitude as that of BeGa, that is, mid-10^{17} cm$^{-3}$ or above. Hence, the direct mechanism (Be_Ga → V_Ga + Be_i) is the more likely process behind the V_Ga generation during annealing of the thin films. For this process to be important after 2 h at 900°C but inefficient at 700°C (the growth temperature), the activation energy can be estimated as $E_A = 3.5 ± 0.5$ eV.

The amphoteric behavior of Be, involving switching from a substitutional to an interstitial position, also explains the data in the HNPS bulk crystals that are grown at much higher temperatures than the MBE thin films. Both in the high-O and low-O cases, the Be impurities are substitutional at low temperatures and interstitial at high temperatures, thus promoting V_Ga formation. However, only in the high-O case do the Ga vacancies survive the cooling from the growth temperature through efficient formation of complexes with O.\[35\] This is in excellent agreement with the recent results obtained by combining pressure-dependent photoluminescence experiments with theoretical calculations, showing the dominance of BeGa and BeGa-O_N-related optical signatures in the low-O HNPS bulk crystals.\[36\] The concentration of V_Ga-related defects was found to correlate with the Be concentration; adding Be to the growth environment promotes V_Ga formation even with the presence of a very high Be concentration\[31,37\]. This finding reveals a rather surprising difference between Mg and Be acceptors in GaN: while high Mg doping prevents Ga vacancy formation, Be at high enough concentrations and temperatures promotes it\[38\]. In addition, most of the Be must be in substitutional sites after cooling to passivate the donor character of the O impurities, furthering evidence for switching between substitutional and interstitial sites working in both directions. Remarkably, similar thermal
and Fermi-level dependent competition between substitutional and interstitial sites has also been observed for Na and Li in ZnO [39,40]. Metal-substituting light atom dopants have also been suggested to exhibit similarities in their electronic properties in GaN and ZnO [4].

In summary, we show that Be exhibits amphoteric behavior in GaN, involving switching between substitutional (acceptor) and interstitial (donor) positions in the lattice. This is observed through the dominance of BeGa in the positron annihilation signals in Be-doped GaN. Subjecting the material to high enough temperatures drives the Be impurities to interstitial positions, observed through the emergence of V_{Ga}\textsuperscript{+}-related defects in concentrations comparable to those of BeGa. The thermal switching between interstitial and substitutional sites of Be appears reversible, as Be-doped GaN is predominantly semi-insulating before and after subjection to high temperatures. We suggest this behavior to be a universal property of light atom dopants substituting for heavy cations in compound semiconductors.

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